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**TELECOPIER TRANSMITTAL FORM**

**DATE:** August 5, 2002  
**TO:** Examiner Michelle Estrada  
**FIRM:** USPTO/Group Art Unit 2823  
**CITY, STATE:**  
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**FROM:** Kathleen Smith

**TOTAL NUMBER OF PAGES: 5**  
**(INCLUDING THIS PAGE)**

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**MESSAGE:****FAX COPY RECEIVED****Applicant(s): Raffaele ZAMBRANO****Serial No. 09/191,743****For: IN-SITU DEPOSITION AND DOPING PROCESS FOR  
POLYCRYSTALLINE SILICON LAYERS AND THE RESULTING DEVICE****AUG 5 2002**  
TECHNOLOGY CENTER 2800

Dear Examiner:

Per your request, enclosed is a DUPLICATE COPY of the Supplemental Response that we filed via mail on July 10, 2002.

Certainly do not hesitate to contact us if you have any questions or comments.

Sincerely,



Kathleen Smith  
Patent Paralegal

CONFIDENTIALITY NOTE: THE INFORMATION CONTAINED IN THIS TRANSMISSION IS LEGALLY PRIVILEGED AND CONFIDENTIAL, INTENDED ONLY FOR THE USE OF THE INDIVIDUAL OR ENTITY NAMED ABOVE. IF THE READER OF THIS MESSAGE IS NOT THE INTENDED RECIPIENT, YOU ARE HEREBY NOTIFIED THAT ANY DISSEMINATION, DISTRIBUTION, OR COPYING OF THIS COMMUNICATION IS STRICTLY PROHIBITED. IF YOU RECEIVE THIS COMMUNICATION IN ERROR, PLEASE NOTIFY US IMMEDIATELY BY TELEPHONE (COLLECT) AND RETURN THE ORIGINAL MESSAGE TO US AT THE ABOVE LISTED ADDRESS VIA THE U.S. POSTAL SERVICE. WE WILL REIMBURSE YOU FOR POSTAGE AND/OR TELEPHONE EXPENSES INVOLVED. THANK YOU.

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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Serial No. 09/191,743

Filing Date: November 13, 1998

For: *IN-SITU DEPOSITION AND DOPING PROCESS FOR POLY-  
CRYSTALLINE SILICON LAYERS AND THE RESULTING DEVICE*

**Enclosed are the following:**

Supplemental Response; and 1 Sheet of Formal Drawings (Figs. 1-2d)

**Docket No. 97-CT-174**

**220-X99-086**

**July 10, 2002**

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